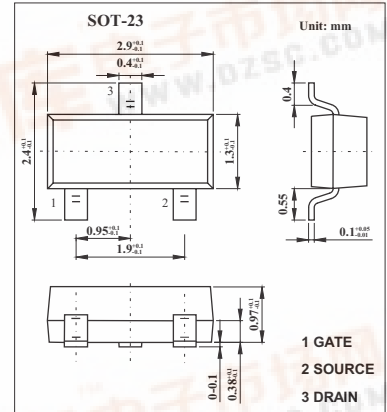


SMD Type MOSFET

MOS Fied Effect Transistor  
2SJ209

■ Features

- Directly driven by Ics having a 5V poer supply.
- Not necessary to consider driving current because of its high input impedance.
- Possible to reduce the number of parts by omitting the biasresistor.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage V <sub>GS</sub> =0	V <sub>DSS</sub>	-100	V
Gate to source voltage V <sub>DS</sub> =0	V <sub>GSS</sub>	± 16	V
Drain current (DC)	I <sub>D</sub>	± 100	m A
Drain current(pulse) *	I <sub>D</sub>	± 200	m A
Power dissipation	P <sub>D</sub>	200	m W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\* PW ≤ 10 ms; d ≤ 50%.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> =-100V, V <sub>GS</sub> =0			-10	μ A
Gate leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =± 16V, V <sub>DS</sub> =0			± 10	μ A
Gate cut-off voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-5.0V, I <sub>D</sub> =-1 μ A	-1.5	-2.0	-2.5	V
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> =-5.0V, I <sub>D</sub> =-10mA	15	22		ms
Drain to source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.0V, I <sub>D</sub> =-10mA		60	100	Ω
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-10mA		37	60	Ω
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-5.0V, V <sub>GS</sub> =0, f=1MHZ		17		pF
Output capacitance	C <sub>oss</sub>		9		pF	
Reverse transfer capacitance	C <sub>rss</sub>		1		pF	
Turn-on delay time	t <sub>d(on)</sub>		45		ns	
Rise time	t <sub>r</sub>	V <sub>GS(on)</sub> =-4V, R <sub>G</sub> =10 Ω, V <sub>DD</sub> =-5V, I <sub>D</sub> =-10mA R <sub>L</sub> =500 Ω		75		ns
Turn-off delay time	t <sub>d(off)</sub>		25		ns	
Fall time	t <sub>f</sub>		80		ns	

■ Marking

Marking	H17
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